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rfmd.com

# **SZA-5044(Z)**

#### 4.9 GHz to 5.9 GHz 5V POWER AMPLIFIER



Package: QFN, 4mmx4mm

### **Product Description**

RFMD's SZA-5044 is a high efficiency class AB Heterojunction Bipolar Transistor (HBT) amplifier housed in a low-cost surface-mountable plastic package. This HBT amplifier is made with InGaP on GaAs device technology and fabricated with MOCVD for an ideal combination of low cost and high reliability. This product is specifically designed as a final or driver stage for 802.11a equipment in the  $4.9 \, \text{GHz} \, \text{to} \, 5.9 \, \text{GHz}$  band for a 5V supply. Optimized on-chip impedance matching circuitry provides a  $50 \, \Omega$  nominal RF input impedance. A single external output matching circuit covers the entire  $4.9 \, \text{GHz} \, \text{to} \, 5.9 \, \text{GHz}$  band simultaneously. The external

Optimum Technology Matching® Applied

GaAs HBT

GaAs MESFET

✓ InGaP HBT

SiGe BiCMOS

Si BiCMOS

SiGe HBT

GaAs pHEMT

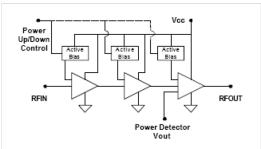
Si CMOS

Si BJT

GaN HEMT

RF MEMS

output match allows for load line optimization for other applications or optimized performance over narrower bands. This product is available in a RoHS Compliant and Green package with matte tin finish, designated by the "Z" package suffix.



#### **Features**

- 802.11a 54Mb/s Class AB Performance P<sub>OUT</sub>=22dBm at 3% EVM, 5V, 343mA
- High Gain=33dB
- Output Return Loss >11dB for Linear Tune
- On-Chip Output Power Detector
- P<sub>1dB</sub>=30dBm at 5V
- Simultaneous 4.9 GHz to 5.9 GHz Performance
- Robust Survives RF Input Power =+15dBm
- Power Up/Down Control <1ms, V<sub>PC</sub> 2.9Vto5V

### **Applications**

- 802.11a WiFi. OFDM
- 5.8GHz ISM Band, 802.16 WiMAX

Parameter	Specification			Unit	Condition	
raiailletei	Min.	Тур.	Max.	UIIIL	Condition	
Frequency of Operation	4900		5900	MHz		
Output Power at 1dB Compression		30.2		dBm	5.15 GHz	
	27.5	29.0		dBm	5.875GHz	
Gain	30.7	32.7	34.7	dB	4.9 GHz	
		33.0		dB	5.15GHz	
	25.7	27.7	29.7	dB	5.875 GHz	
Output Power		21.0		dBm	3% EVM 802.11a 54Mb/s-5.15GHz	
		22.0		dBm	3% EVM 802.11a 54Mb/s-5.875GHz	
Noise Figure		6.3		dB	5.875 GHz	
Third Order Intermod		-39.0	-35.0	dBc	5.875GHz, 18dBm per tone	
Worst Case Input Return Loss	8.6	11.6		dB	4.9 GHz to 5.875 GHz	
Worst Case Output Return Loss	9.3	12.3		dB	4.9GHzto5.875GHz	
Output Voltage Range		0.8 to 1.9		V	P <sub>OUT</sub> =10dBmto26dBm	
V <sub>CC</sub> Quiescent Current	230	270	310	mA		
Power Up Control Current		1.7		mA	V <sub>PC</sub> =5V (I <sub>VPC1</sub> +I <sub>VPC2</sub> +I <sub>VPC3</sub> )	
Off V <sub>CC</sub> Leakage Current		8	100	uA	V <sub>PC</sub> =0V	
Thermal Resistance (junction-lead		24		°C/W	junction - lead	
802.11ac Output power		21.0		dBm	1.8% EVM 802.11ac HT80 MCS9 5.21GHz to 5.77GHz	
802.11ac Operating Current		330		mA	P <sub>OUT</sub> =21dBm	

Test Conditions:  $Z_0 = 50 \Omega$ ,  $V_{CC} = 5 V$ ,  $I_{CO} = 270 \text{ mA}$ ,  $T_{BP} = 25 ^{\circ}\text{C}$ 



#### **Absolute Maximum Ratings**

Parameter	Rating	Unit
VC3 Collector Bias Current (pin 16)	500	mA
VC2 Collector Bias Current (pin 18)	225	mA
VC1 Collector Bias Current (pin 19)	75	mA
Device Voltage (V <sub>D</sub> ), No RF drive	7.0	V
Power Dissipation	3.4	W
Operating Lead Temperature (T <sub>L</sub> )	-40to+85	°C
RF Input Power for $50\Omega$ RF out load	15	dBm
RF Input Power for 10:1 VSWR RF out load	2	dBm
Storage Temperature Range	-40to+150	°C
Operating Junction Temperature (T <sub>J</sub> )	150	°C
ESD Rating - Human Body Model (HBM)	>1000	V

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one. Bias Conditions should also satisfy the following expression:  $I_DV_D\!<\!(T_J\!-\!T_L)/R_{TH},j\!-\!I$ 



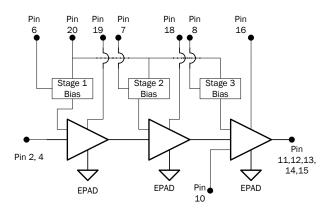
Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EUDirective 2002/95/EC (at time of this document revision).

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## **Simplified Device Schematic**



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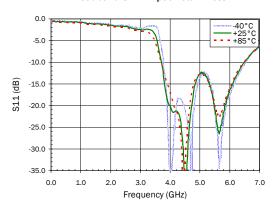
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Pin	Function	Description
1, 3,	N/C	Pins are not used. May be grounded, left open, or connected to adjacent pin.
5, 9,	, -	
11,		
<b>15, 17</b>		
6	VPC1	VPC1 is the bias control pin for the stage 1 active bias circuit and can be run from 2.9Vto5V control. An external series resistor is required for proper setting of bias levels depending on control voltage. Refer to the evaluation board schematic for resistor value. To prevent potential damage, do not apply voltage to this pin that is +1V greater than voltage applied to pin 20 (Vbias) unless Vpc supply current capability is less than 10 mA.
7	VPC2	VPC2 is the bias control pin for the stage 2 active bias circuit and can be run from 2.9Vto5V control. An external series resistor is required for proper setting of bias levels depending on control voltage. Refer to the evaluation board schematic for resistor value. To prevent potential damage, do not apply voltage to be pin that is +1V greater than voltage applied to pin 20 (Vbias) unless Vpc supply current capability is less than 10 mA.
8	VPC3	VPC3 is the bias control pin for the stage 3 active bias circuit and can be run from 2.9Vto5V control. An external series resistor is required for proper setting of bias levels depending on control voltage. Refer to the evaluation board schematic for resistor value. To prevent potential damage, do not apply voltage to this pin that is +1V greater than voltage applied to pin 20 (Vbias) unless Vpc supply current capability is less than 10mA.
10	VDET	Output power detector voltage. Load with 10 K to 100 K $\Omega$ to ground for best performance.
2, 4	RF IN	RF input pins. This is DC grounded internal to the IC. Do not apply voltage to this pin. All three pins must be used for proper operation.
12,	RF OUT	RF output pin. This is also another connection to the 3rd stage collector
13,14		
16	VC3	3rd stage collector bias pin. Apply 5V to this pin.
18	VC2	2nd stage collector bias pin. Apply 5V to this pin.
19	VC1	1st stage collector bias pin. Apply 5 V to this pin.
20	VBIAS	Active bias network VCC. Apply 5V to this pin.
EPAD	GND	Exposed area on the bottom side of the package needs to be soldered to the ground plane of the board for optimum thermal and RF performance. Several vias should be located under the EPAD as shown in the recommended land pattern (page 5).

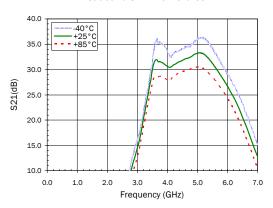


#### 4.9 GHz to 5.9 GHz Evaluation Board Data ( $V_{BIAS}$ =5.0 V, $I_{Q}$ =270 mA)

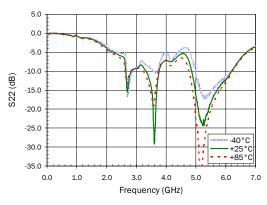
**Broadband S11 - Input Return Loss** 



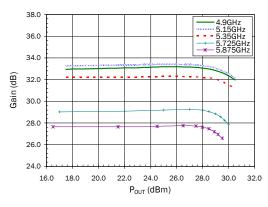
**Broadband S21 - Forward Gain** 



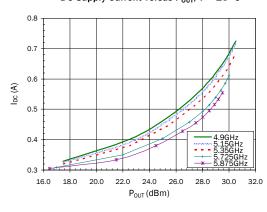
**Broadband S22 - Output Return Loss** 



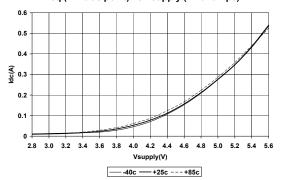
Typical Gain versus Pout, T=+25°C



DC Supply Current versus P<sub>OUT</sub>, T=+25 °C

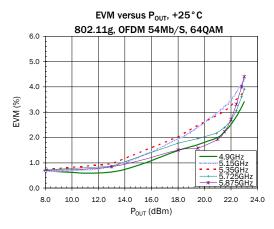


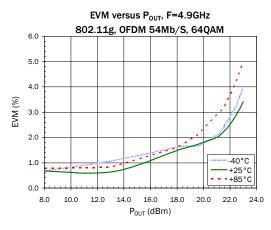
Icq (DC bias point) vs Vsupply (V+ and Vpc)

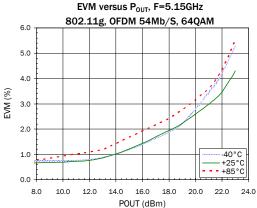


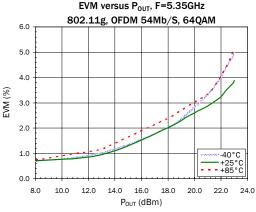


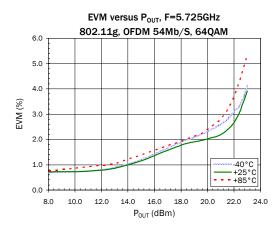
4.9 GHz to 5.9 GHz Evaluation Board Data (V<sub>BIAS</sub>=5.0V, I<sub>Q</sub>=270 mA) 802.11a EVM, 0FDM,  $54\,\text{Mb/s}$ ,  $64\,\text{QAM}$ 

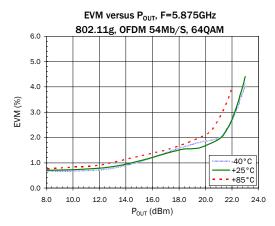






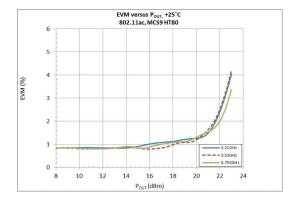


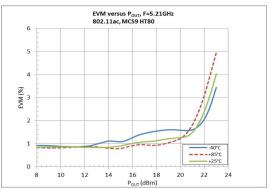


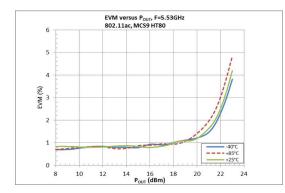


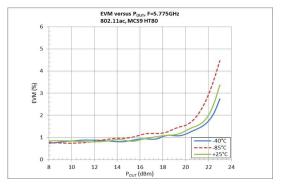


#### $5.21\,\mathrm{GHz}$ to $5.775\,\mathrm{GHz}$ Evaluation Board Data (V\_BIAS=5.0V, I\_Q=270\,\mathrm{mA}) 802.11ac EVM, HT80 MCS9



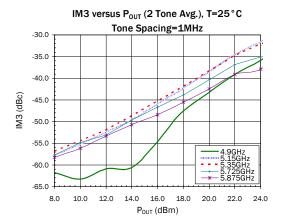


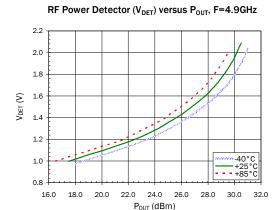


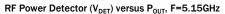


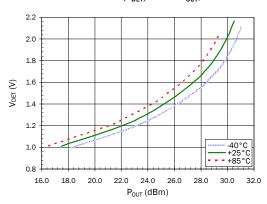


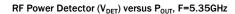
#### 4.9 GHz to 5.9 GHz Evaluation Board Data ( $V_{BIAS}$ =5.0 V, $I_{Q}$ =270 mA)

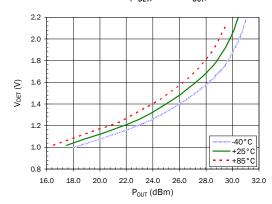




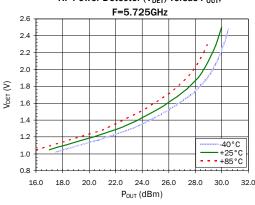




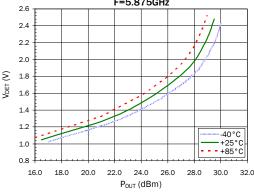




### RF Power Detector ( $V_{DET}$ ) versus $P_{OUT}$ ,

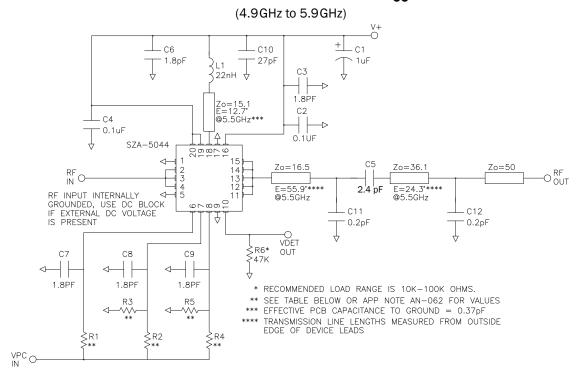


RF Power Detector (V<sub>DET</sub>) versus P<sub>OUT</sub>, F=5.875GHz





### Evaluation Board Schematic for V+=V<sub>CC</sub>=5.0V



Notes: Pins 1, 3, 5, 9, 11, 15, and 17 are unwired (N/C) inside the package. Refer to page 2 for detailed pin descriptions. Some of these pins are wired to adjacent pins or grounded as shown in the application circuit. This is to maintain consistence with the evaluation board layout shown below. It is recommended to use this layout and wiring to achieve the specified performance.

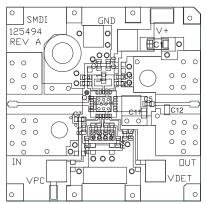
To prevent potential damage, do not apply voltage to the  $V_{PC}$  pin that is +1V greater than voltage applied to pin 20 ( $V_{BIAS}/V_{CC}$ ) unless  $V_{PC}$  supply current capability is less than 10 mA.



### Evaluation Board Layout for V+=V<sub>CC</sub>=5.0V

(4.9 GHz to 5.9 GHz)

Board material GETEK, 10 mil thick, Dk = 3.9, 2 oz. copper finish



PCB notes: Do not use less than recommended ground via holes.

RF Layers thicker than.020 inches (0.5 mm) not recommended.

DESG	Description
Q1	SZA-5044
R1, 2, 3, 4, 5, 6	1%, 0402
C1	IuF 15V TANTALUM CAP
C2, 4	0.1 uF CAP, 0402
C3, 6, 7, 8, 9	1.8 pF Cap, 0402
C5	2.4 pF Cap, 0402
C10	27 pF Cap, 0402
L1	22nH IND, 0402
C11, 12	0.2 pF Cap, 0603

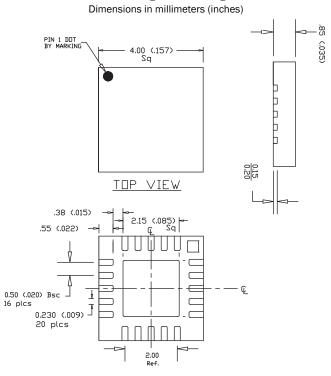
Resistor values for  $V_{PC}$ =2.9 V to 5 V ( $V_{CC}$ =5 V,  $I_{Q}$ =270 mA)

VPC(V)	R1	R2	R4	R3	R5
2.9	0	698	10	OUT	OUT
3.0	174	1.1K	281	OUT	OUT
3.1	348	1.37 K	499	OUT	OUT
3.2	511	1.78K	750	OUT	OUt
3.3	698	2.15 K	1.00 K	OUT	OUT
5.0	3.6K	2.2K	2.4K	7.5 K	7.5 K

Note: See app note for  $V_{CC}$  and  $V_{PC}$  combinations



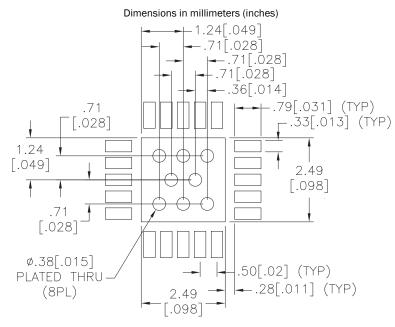
### **Package Drawing**



BOTTOM VIEW

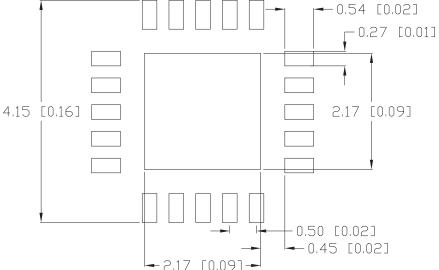


#### **Recommended Land Pattern**



### Recommended PCB Soldermask (SMBOC) for Land Pattern







#### Part Symbolization

The part will be symbolized with an "SZA-5044" for Sn/Pb plating or "SZA-5044Z" for RoHS green compliant product. Marking designator will be on the top surface of the package.

### **Ordering Information**

Ordering Code	Description
SZA5044ZSQ	Standard 25 piece bag
SZA5044ZSR	Standard 100 piece reel
SZA5044Z	Standard 1000 piece reel
SZA5044Z-EVB1	Evaluation Board 4.9GHz to 5.9 GHz Tune